

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1. (currently amended) A method for forming a T-shaped conductive wire of a semiconductor device, comprising:

etching a lower portion of a side wall of a silicon layer ~~pattern by using a notching phenomenon~~ based on a difference ~~[[of]]between an etching selectivities between rate of a silicon layer and an etching rate of a lower film to form a T-shaped silicon layer pattern~~; and

forming a T-shaped conductive wire based on the T-shaped silicon layer pattern.

2. (currently amended) The method of claim 1, wherein the lower ~~layer-film~~ comprises an insulating material, wherein ~~[[the]]~~ an etching selectivity ratio of the insulating material to ~~that of the silicon layer~~ is 1:5 to 1:500.

3-14. (canceled)